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TITLE: Process for cleaning showerhead for a chemical vapor deposition chamber

INVENTOR: JU, T ; RUAN, J ; SHR, H ; YANG, N

AGENT-ASSIGNEE:

SSIGNEE

CODE

INBOND ELECTRONICS CORP

WINBN

PRIORITY-DATA: 1999TW-0108628 (May 26, 1999)

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AGENT-FAMILY:

PUB-NO	PUB-DATE	LANGUAGE	PAGES	MAIN-IPC
TW 460611 A	October 21, 2001		000	C23C016/52

APPLICATION-DATA:

PUB-NO	APPL-DATE	APPL-NO	DESCRIPTOR
TW 460611A	May 26, 1999	1999TW-0108628	

INT-CL (IPC): C23 C 16/52

EXTRACTED-PUB-NO: TW 460611A

ASIC-ABSTRACT:

NOVELTY - The present invention provides a process for cleaning a showerhead for a chemical vapor deposition chamber. First, the showerhead is dipped into an alkaline reagent containing ammonium water so as to remove aluminum fluoride attached on the showerhead. Subsequently, the residual alkaline reagent remaining on the showerhead is removed. The showerhead is made of an aluminum-containing component, and the aluminum fluoride is obtained from the reaction of a plasma of a fluorine-containing gas used for cleaning the chamber and aluminum. By using the ammonia water-containing alkaline reagent, the showerhead for a chemical vapor deposition chamber can be effectively cleaned. Thus, the process stability can be increased and the life span of the showerhead can be lengthened.

HOSEN-DRAWING: Dwg.0/1

TITLE-TERMS: PROCESS CLEAN CHEMICAL VAPOUR DEPOSIT CHAMBER

DERWENT-CLASS: M12

DPI-CODES: M12-A05;